

30V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C
001/	2.2mΩ @ V _{GS} = 10V	170A
30V	$3.2m\Omega$ @ $V_{GS} = 4.5V$	140A

Description and Applications

This new generation MOSFET is designed to minimize $R_{DS(ON)}$, yet maintain superior switching performance. This device is ideal for use in power management and load switch.

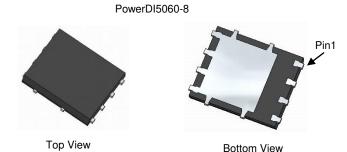
- DC-DC Converters
- Load Switch

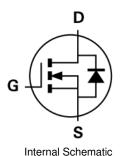
Features

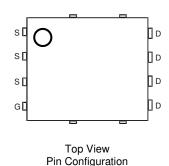
- Thermally Efficient Package-Cooler Running Applications
- <1.1mm Package Profile Ideal for Thin Applications
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMTH32M5LPSQ)

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.097 grams (Approximate)







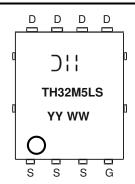
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH32M5LPS-13	PowerDI5060-8	2,500 / Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



);; = Manufacturer's Marking TH32M5LS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 18 = 2018) WW = Week (01 to 53)

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Maximum Ratings (@T_C = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	30	V		
Gate-Source Voltage	V_{GSS}	±16	V		
Continuous Drain Current, V _{GS} = 10V (Note 6)	Ι _D	170 120	Α		
Maximum Continuous Body Diode Forward Current (Note	Is	80	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	350	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	350	Α
Avalanche Current, L = 0.1mH			I _{AS}	50	Α
Avalanche Energy, L = 0.1mH			Eas	140	mJ

Thermal Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	3.2	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	54	°C/W	
Total Power Dissipation (Note 6)	P_{D}	100	W	
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	1.5	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_C = +25°C, unless otherwise specified.)

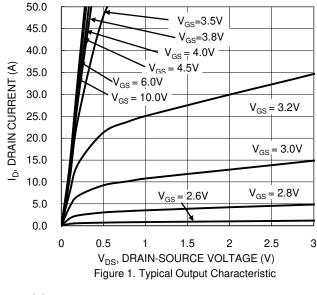
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	V _{DS} = 24V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)						•	
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	٧	$V_{DS} = V_{GS}$, $I_D = 1mA$	
Static Drain-Source On-Resistance		_	1.6	2.2	mΩ	$V_{GS} = 10V, I_D = 30A$	
Static Drain-Source On-nesistance	R _{DS(ON)}	_	2.6	3.2	11122	$V_{GS} = 4.5V, I_D = 30A$	
Diode Forward Voltage	V _{SD}	_	0.8	1.1	V	$V_{GS} = 0V, I_S = 30A$	
DYNAMIC CHARACTERISTICS (Note 8)						•	
Input Capacitance	C _{iss}		3944			V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	1267	_	рF		
Reverse Transfer Capacitance	C _{rss}	_	186	_			
Gate Resistance	R_{g}	_	0.6	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	34	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	68	_	nC	V 45V L 00A	
Gate-Source Charge	Q_{gs}	_	8	_	IIC	$V_{DS} = 15V, I_D = 20A$	
Gate-Drain Charge	Q_{gd}	_	15	_			
Turn-On Delay Time	t _{D(ON)}	_	7.2	_			
Turn-On Rise Time	t _R	_	13.2	_		$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	37.5	_	ns	$I_D = 15A$, $R_G = 3\Omega$	
Turn-Off Fall Time	t _F	_	23.9	_			
Body Diode Reverse Recovery Time	t _{RR}	_	28.7	_	ns	1 15A di/dt 500A/	
Body Diode Reverse Recovery Charge	Q _{RR}	_	45.8	_	nC	$I_S = 15A$, di/dt = 500A/ μ s	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.6. Thermal resistance from junction to soldering point (on the exposed drain pad).7. Short duration pulse test used to minimize self-heating effect. Notes:

^{8.} Guaranteed by design. Not subject to production testing.







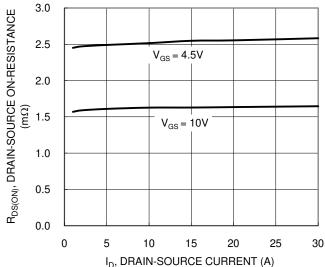


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

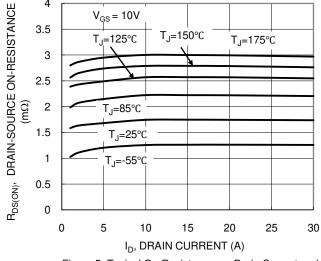


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

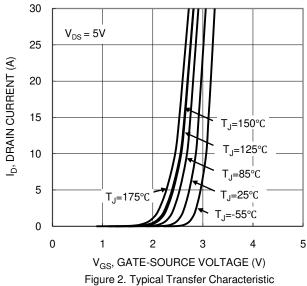


Figure 2. Typical Transfer Characteristic

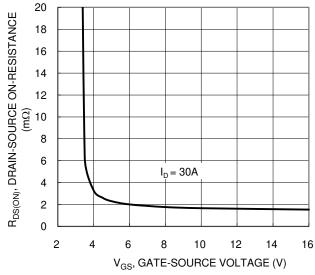


Figure 4. Typical Transfer Characteristic

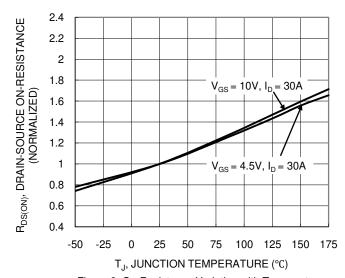


Figure 6. On-Resistance Variation with Temperature



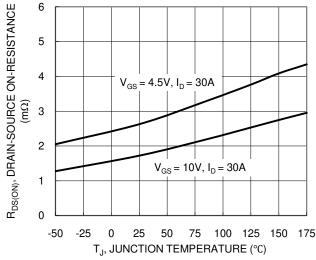


Figure 7. On-Resistance Variation with Temperature

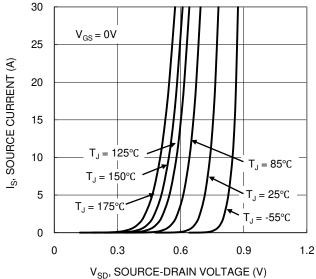
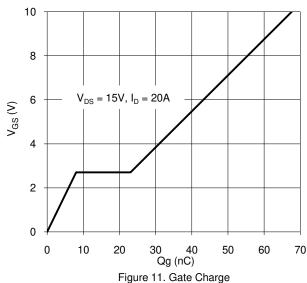


Figure 9. Diode Forward Voltage vs. Current



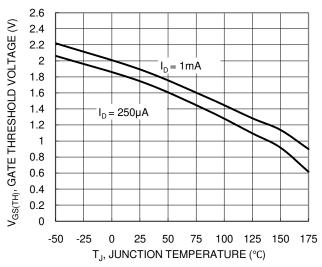


Figure 8. Gate Threshold Variation vs. Junction Temperature

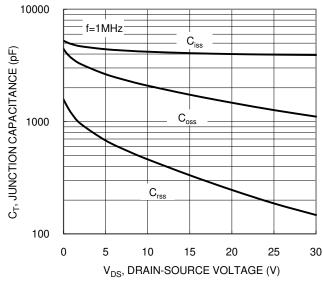
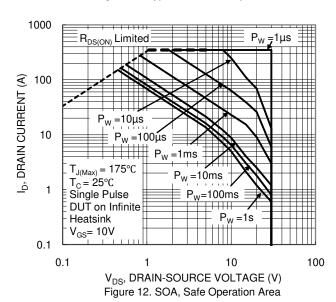


Figure 10. Typical Junction Capacitance





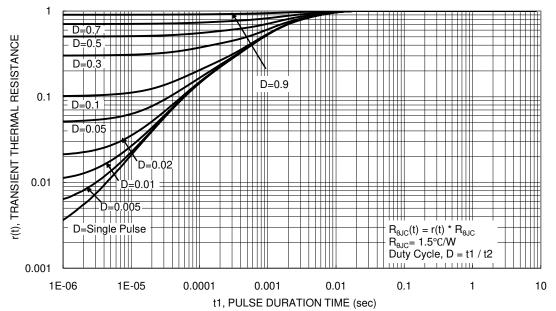


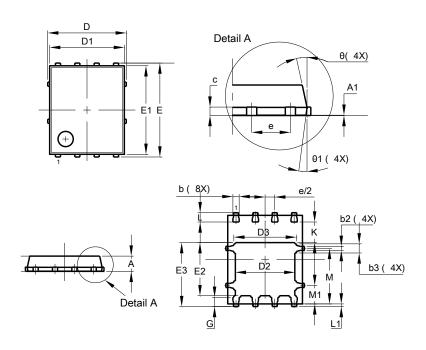
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

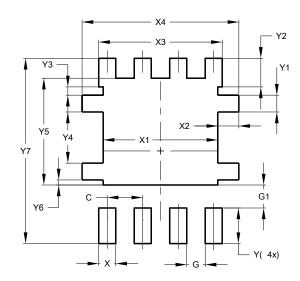


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A 1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D		5.15 BSC	,		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	(6.15 BSC	,		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е		1.27 BSC	,		
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
M	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Υ	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610



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